CLAIM AMENDMENTS:

Please amend Claim 1 as follows:

1. (Currently Amended) A photoelectric converting apparatus comprising:

a sensor unit including a plurality of pixels each having at least a photoelectric converter and a first amplification transistor for amplifying a signal derived from said photoelectric converter to output the amplified signal; and

a memory unit including a plurality of memories each having at least a storage element for storing therein the signal derived from said sensor unit and a second amplification transistor for amplifying a signal derived from said storage element to output an amplified signal

wherein, each of said first and second amplification transistors has a DC gain and an AC gain, wherein ~~at least one of~~ said DC gain ~~and said AC gain~~ differs between said first and second amplification transistors, and wherein said sensor unit and said memory unit output respective signals with a same gain.

2. (Previously Presented) A photoelectric converting apparatus according to Claim 1, wherein said first and said second amplification transistors are constituted by MOS transistors.

3. (Previously Presented) A photoelectric converting apparatus according to Claim 2, wherein said first and said second amplification transistors are connected to respective load MOS transistors.

4. (Previously Presented) A photoelectric converting apparatus according to Claim 3, wherein a conductance of the load MOS transistor connected to said first amplification transistor is different from a conductance of the load MOS transistor connected to said second amplification transistor.

5. (Previously Presented) A photoelectric converting apparatus according to Claim 4, wherein respective gate lengths of said load MOS transistors differ.

6. (Previously Presented) A photoelectric converting apparatus according to Claim 4, wherein respective gate widths of said load MOS transistors differ.

7. (Previously Presented) A photoelectric converting apparatus according to Claim 4, respective gate oxide layer thicknesses of said load MOS transistors differ.

8. (Previously Presented) A photoelectric converting apparatus according to Claim 3, wherein respective conductances of said first and second amplification transistors differ.

9. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate lengths of said first and second amplification transistors differ.

10. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate widths of said first and second amplification transistors differ.

11. (Previously Presented) A photoelectric converting apparatus according to Claim 8, wherein respective gate oxide layer thicknesses of said first and second amplification transistors differ.

12. (Previously Presented) A photoelectric converting apparatus according to Claim 1, further comprising a transferring system for amplifying the signal derived from said sensor unit and/or said memory unit to transfer the amplified signal to said sensor unit and/or said memory unit.